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**Roll No. ....**

## **TEC-201**

**B. TECH. (SECOND SEMESTER)**

**MID SEMESTER**

**EXAMINATION, 2021-22**

**BASIC ELECTRONICS ENGINEERING**

**Time : 1½ Hours**

**Maximum Marks : 50**

**Note :** (i) Answer all the questions by choosing any *one* of the sub-questions.

(ii) Each sub-question carries 10 marks.

1. (a) Why NAND and NOR gates are called universal gates ? Realize NOR, OR, AND gates using NOR gates only. (CO1)

OR

- (b) Perform the following number system conversions : (CO1)

(i)  $(21.3)_{10} = (?)_2$

**P. T. O.**

$$(ii) (C1A)_{16} = (?)_2$$

$$(iii) (11.1)_2 = (?)_{10}$$

$$(iv) (74)_{10} = (?)_8$$

$$(v) (101001)_2 = (?)_8$$

2. (a) Write and explain the laws of Boolean algebra. (CO1)

OR

- (b) (i) Minimize using Boolean algebra : (CO1)

$$f(A, B, C) = A'B'C' + A'BC' + AB'C' + ABC'$$

- (ii) Minimize using K-map :

$$f(A, B, C, D) = \sum m(3, 5, 7, 11, 13, 15)$$

3. (a) (i) Express  $f(A, B, C) = AB + BC'$  in canonical SOP form. (CO1)
- (ii) Express  $f(A, B, C) = (A' + C')(A + B')$  in canonical POS form.

OR

- (b) Perform the following in binary : (CO1)
- (i)  $(14)_{10} - (9)_{10}$  using 1's complement
- (ii)  $(10)_{10} - (4)_{10}$  using 2's complement

(3)

4. (a) Write short notes on the following : (CO2)

(i) Mobility

(ii) Conductivity

(iii) Current density

OR

(b) Draw and discuss the V-I characteristics of P-N junction diode. What do you mean by the breakdown voltage of diode ? (CO2)

5. (a) What do you mean by the depletion layer of a P-N junction diode ? Explain how the diode can be forward and reverse biased.

(CO2)

OR

(b) Consider a semiconductor doped with  $7 \times 10^{17}/\text{cm}^3$  donor atom concentration. If mobility of electron is  $800 \text{ cm}^2/\text{V-s}$  and that of hole is  $200 \text{ cm}^2/\text{V-s}$ , calculate the majority and minority carrier concentrations and the final conductivity. (Given : Intrinsic carrier concentration  $= 1.5 \times 10^{10}/\text{cm}^3$ ). (CO2)